



N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) ^e | Q_g (Typ.) |
|--------------|----------------------------|------------------------|--------------|
| 20 | 0.0318 at $V_{GS} = 4.5$ V | 6 ^a | 8.8 nC |
| | 0.0356 at $V_{GS} = 2.5$ V | 6 ^a | |
| | 0.0414 at $V_{GS} = 1.8$ V | 5.6 | |

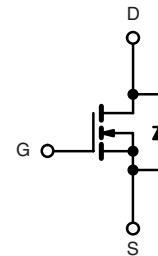
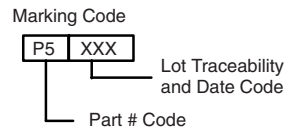
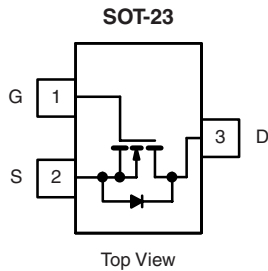
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC


RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- DC/DC Converters
- Load Switch for Portable Applications


Ordering Information: Si2312CDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

| Parameter | Symbol | Limit | Unit |
|--|----------------|----------------------|------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 8 | |
| Continuous Drain Current ($T_J = 150$ °C) | $T_C = 25$ °C | 6 ^a | A |
| | $T_C = 70$ °C | 5.1 | |
| | $T_A = 25$ °C | 5 ^{b, c} | |
| | $T_A = 70$ °C | 4 ^{b, c} | |
| Pulsed Drain Current | I_{DM} | 20 | |
| Continuous Source-Drain Diode Current | $T_C = 25$ °C | 1.75 | |
| | $T_A = 25$ °C | 1.04 ^{b, c} | |
| Maximum Power Dissipation | $T_C = 25$ °C | 2.1 | W |
| | $T_C = 70$ °C | 1.3 | |
| | $T_A = 25$ °C | 1.25 ^{b, c} | |
| | $T_A = 70$ °C | 0.8 ^{b, c} | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C |
| Soldering Recommendations (Peak Temperature) | | 260 | |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Typical | Maximum | Unit |
|---|------------|---------|---------|------|
| Maximum Junction-to-Ambient ^{b, d} | R_{thJA} | 80 | 100 | °C/W |
| Maximum Junction-to-Foot (Drain) | R_{thJF} | 40 | 60 | |

Notes:

- Package limited
- Surface Mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 125 °C/W.
- Based on $T_C = 25$ °C.

Si2312CDS

Vishay Siliconix



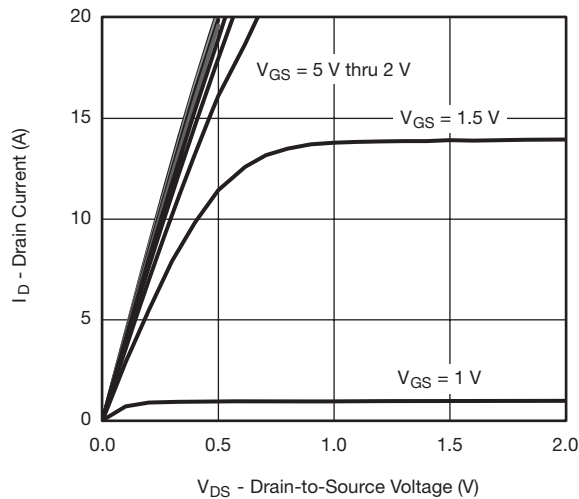
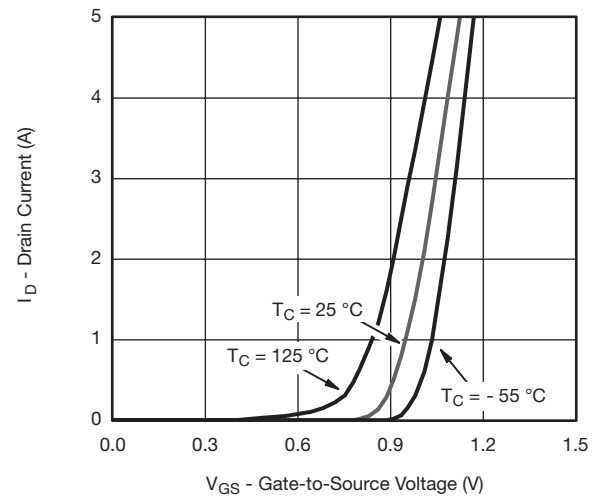
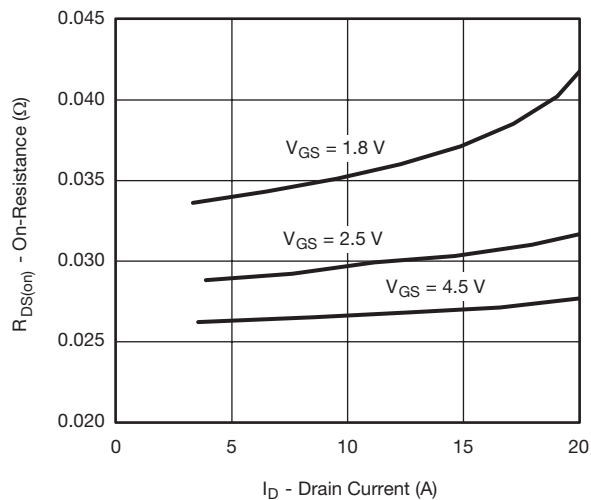
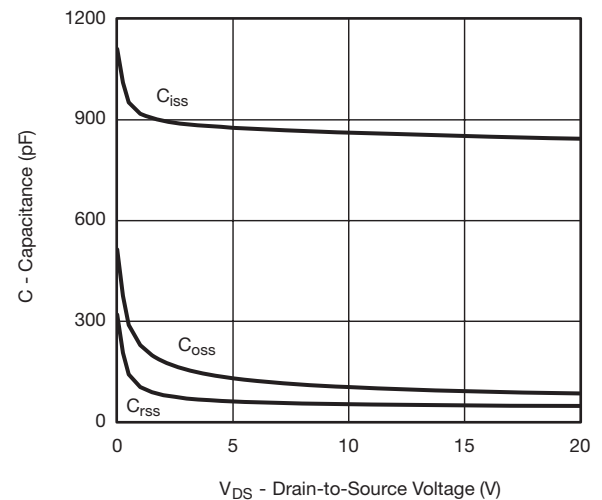
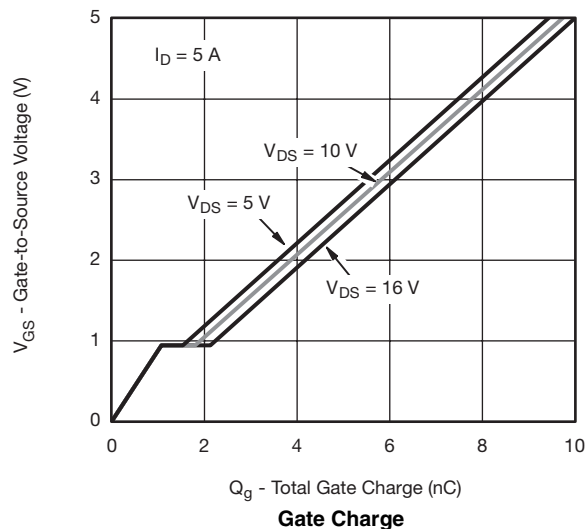
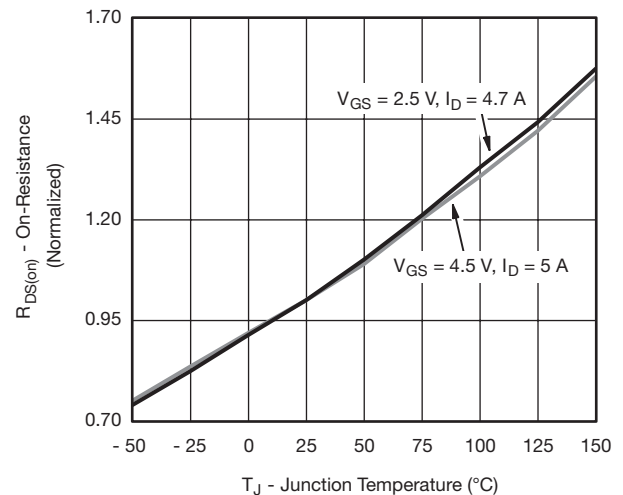
| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | |
|---|--------------------------------------|--|------|--------|--------|-------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | 20 | | | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | I _D = 250 μA | | 25 | | mV/°C |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | | | - 2.6 | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | 0.45 | | 1.0 | V |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 8 V | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 20 V, V _{GS} = 0 V | | | 1 | μA |
| | | V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C | | | 10 | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} ≤ 5 V, V _{GS} = 4.5 V | 20 | | | A |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 4.5 V, I _D = 5.0 A | | 0.0265 | 0.0318 | Ω |
| | | V _{GS} = 2.5 V, I _D = 4.7 A | | 0.0296 | 0.0356 | |
| | | V _{GS} = 1.8 V, I _D = 4.3 A | | 0.0345 | 0.0414 | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = 10 V, I _D = 5.0 A | | 24 | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | | 865 | | pF |
| Output Capacitance | C _{oss} | | | 105 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 55 | | |
| Total Gate Charge | Q _g | V _{DS} = 10 V, V _{GS} = 5 V, I _D = 5.0 A | | 12 | 18 | nC |
| | | V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 5.0 A | | 8.8 | 14 | |
| Gate-Source Charge | Q _{gs} | | | 1.1 | | |
| Gate-Drain Charge | Q _{gd} | | | 0.7 | | |
| Gate Resistance | R _g | f = 1 MHz | 0.5 | 2.4 | 4.8 | Ω |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 10 V, R _L = 2.2 Ω I _D ≡ 4 A, V _{GEN} = 4.5 V, R _g = 1 Ω | | 8 | 16 | ns |
| Rise Time | t _r | | | 17 | 26 | |
| Turn-Off Delay Time | t _{d(off)} | | | 31 | 47 | |
| Fall Time | t _f | | | 8 | 16 | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 10 V, R _L = 2.2 Ω I _D ≡ 4 A, V _{GEN} = 5 V, R _g = 1 Ω | | 5 | 10 | |
| Rise Time | t _r | | | 13 | 20 | |
| Turn-Off Delay Time | t _{d(off)} | | | 21 | 32 | |
| Fall Time | t _f | | | 6 | 12 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | 1.75 | A |
| Pulse Diode Forward Current | I _{SM} | | | | 20 | |
| Body Diode Voltage | V _{SD} | I _S = 4 A, V _{GS} = 0 V | | 0.75 | 1.2 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 4 A, dl/dt = 100 A/μs, T _J = 25 °C | | 12 | 20 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 5 | 10 | nC |
| Reverse Recovery Fall Time | t _a | | | 7 | | ns |
| Reverse Recovery Rise Time | t _b | | | 5 | | |

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

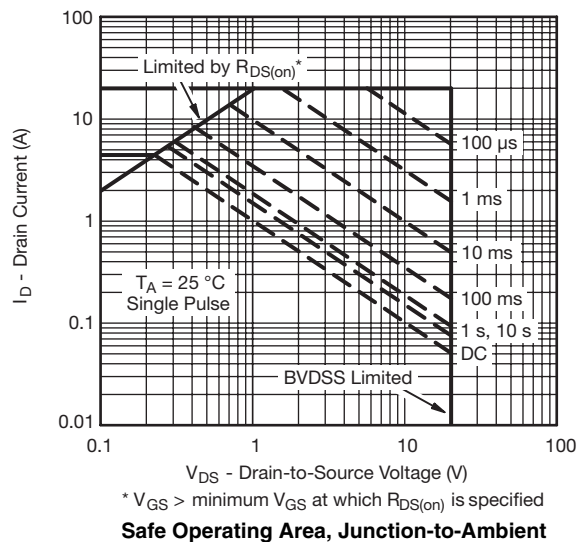
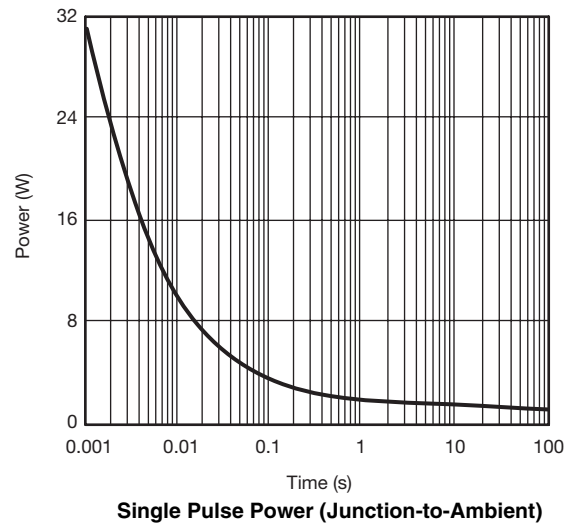
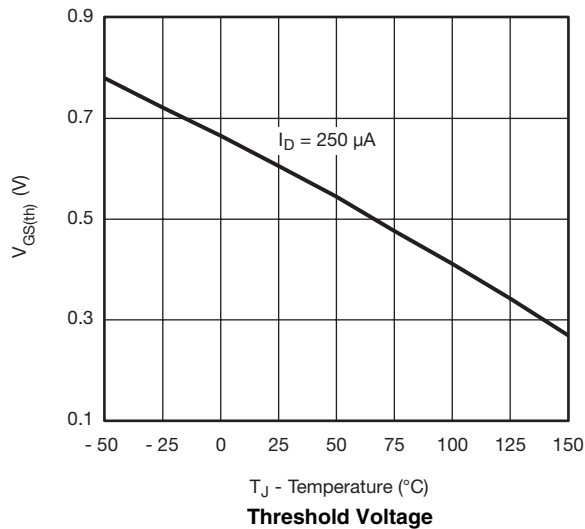
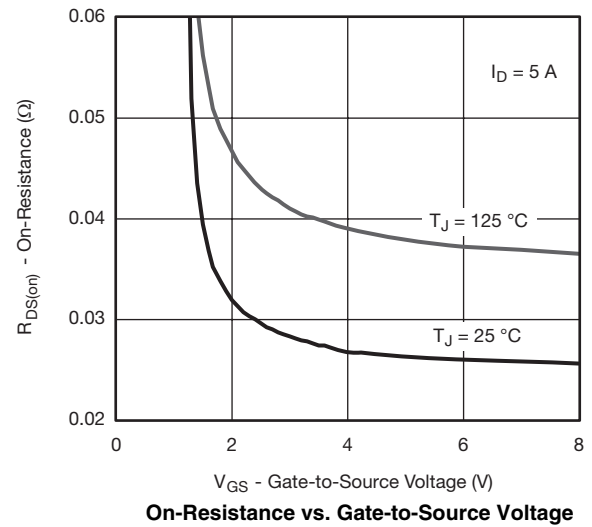
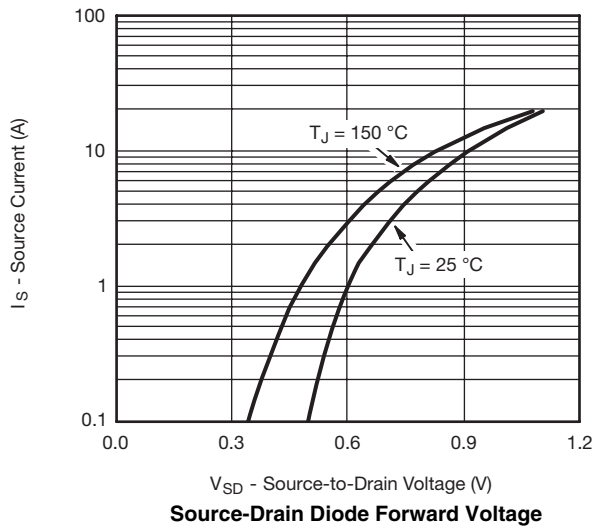
b. Guaranteed by design, not subject to production testing.

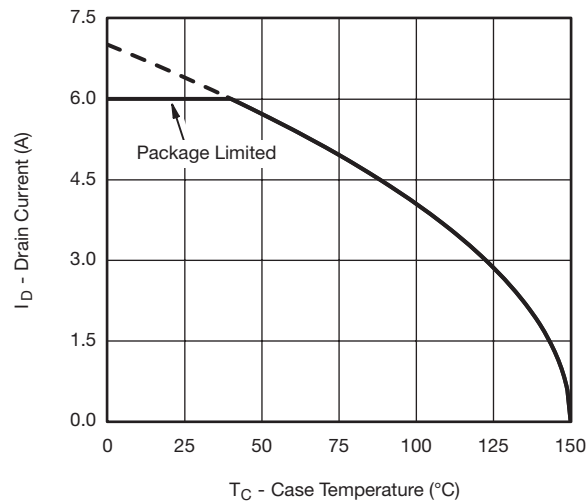
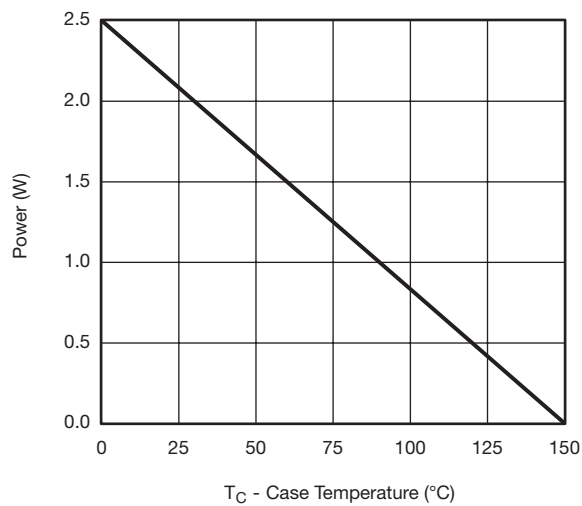
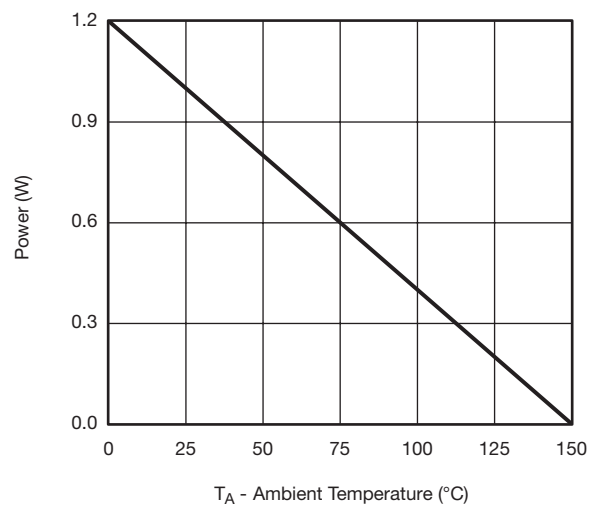
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

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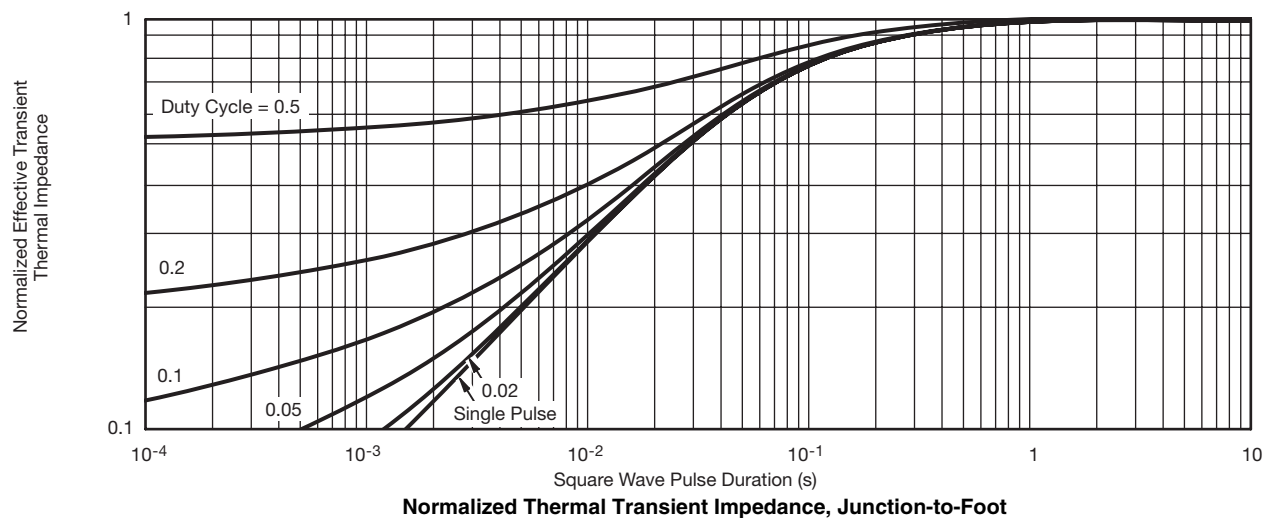
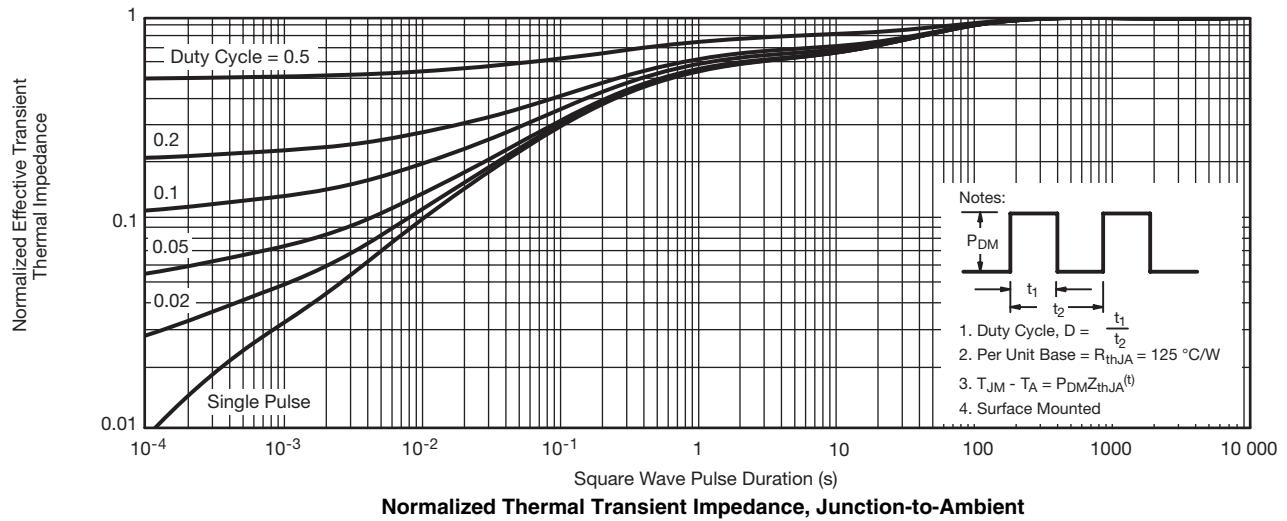
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Current Derating*

Power Derating, Junction-to-Foot

Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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